Sharp to Introduce High-Throughput Combination Memory for Third-Generation Mobile Phones

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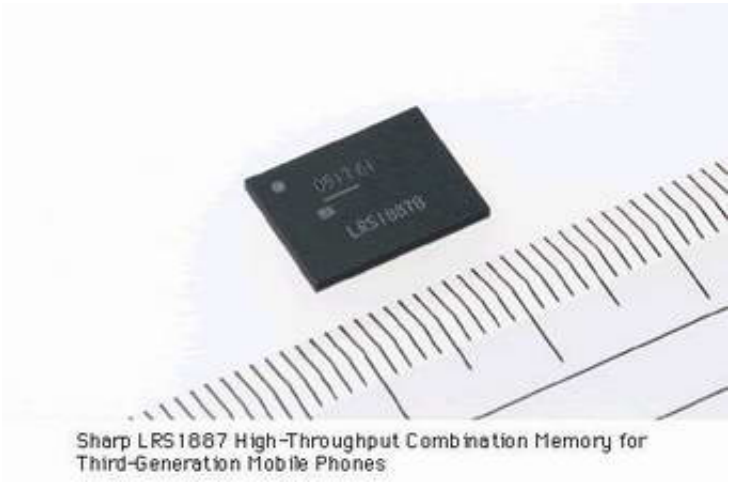
Sharp LRS1887 High-Throughput Combination Memory for Third-Generation Mobile Phones

Sharp Corporation has developed a high-speed combination flash/SCRAM memory device featuring a throughput of 320 MBps (bytes/second), more than three times the transfer rate of its predecessor model. The LRS1887 High-Speed Memory is optimal for advanced third-generation mobile phones as well as other applications requiring high-speed transfer of large volumes of data. Sharp is currently shipping samples of the LRS1887, and will start mass production in July 2005.

As third-generation mobile phones with faster network speeds continue

to evolve, mobile phone hardware is becoming increasingly sophisticated with higher-resolution megapixel CCD cameras, the inclusion of full-motion video functions, and diverse software applications. As such, these enhanced mobile phone functions demand faster processing speeds for large-capacity data.

This newly developed LRS1887 high-capacity 512-Mbit combination flash/SCRAM memory uses an AD Bus that multiplexes the address bus, which specifies the memory access target, onto the data bus that transfers data to the CPU chip. This architecture makes it possible to achieve high-speed data transfers at rates as high as 320 MBps without increasing the number of pins required to make external connections as well as keep the 32-bit bus width.

Incorporating this device in product designs will enable high-speed data transfers, facilitating smooth operation with data-intensive applications such as 3D graphics processing, and will contribute to the evolution of even greater functionality in mobile phones.